EYP-DFB-0763-00010-1500-BFY02-0000



We focus on power.

page 1 from 5

28.11.2011

DFB/DBR

Revision 0.94

DISTRIBUTED FEEDBACK LASER GaAs Semiconductor Laser Diode

with integrated grating structure

General Product Information

Product	Application
763 nm DFB Laser with hermetic Butterfly Housing	Spectroscopy
Monitor Diode, Thermoelectric Cooler and Thermistor	Metrology
PM Fiber with angle-polished Connector	O ₂ Detection
High-reliable fully Space-qualified Package	

Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	Ts	°C	-40		85
Operational Temperature at Case	Tc	°C	-40		85
Operational Temperature at Laser Chip	T _{LD}	°C	10		40
Forward Current	I _F	mA			100
Reverse Voltage	V _R	V			2
Output Power	P _{opt}	mW			12
TEC Current	I _{TEC}	А			1.8
TEC Voltage	V _{TEC}	V			3.2

Recommended Operational Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _c	°C	-20		65
Operational Temperature at Laser Chip	T _{LD}	°C	15		35
Forward Current	I _F	mA			90
Output Power	P _{opt}	mW	2		10

Characteristics at T_{LD} = 25 °C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm	762	763	764
Spectral Width (FWHM)	Δν	MHz		2	
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.06	
Current Coefficient of Wavelength	dλ / dI	nm / mA		0.003	
Output Power @ I _F = 90 mA	P _{opt}	mW	10		



Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Measurement Conditions / Comments measured by integrated Thermistor ex fiber

Meas	urement	Conditio	ns / Com	ments	
	ages on				
	-	-			
ex fibe	er				

© All rights reserved by eagleyard Photonics GmbH. This preliminary data sheet will be electronically administered and is subject to change without notice. Uncontrolled copy when printed. eagleyard Photonics GmbH

Rudower Chaussee 29 12489 Berlin GERMANY fon +49. 30. 6392 4520 fax +49. 30. 6392 4529

info@eagleyard.com www.eagleyard.com



EYP-DFB-0763-00010-1500-BFY02-0000



We focus on power.

page 2 from 5

28.11.2011

DFB/DBR

DISTRIBUTED FEEDBACK LASER

GaAs Semiconductor Laser Diode

Characteristics at T _{amb} 25 °C at Begin Of Life cont					
Parameter	Symbol	Unit	min	typ	max
Slope Efficiency	S	W / A	0.2	0.4	0.7
Threshold Current	I _{th}	mA			70
Sidemode Supression Ratio	SMSR	dB	30	45	
Mode-hop free Temperature Range (SMSR > 3	30 dB)				
Variant 0	T _{LD}	° C		25	
Variant 1	T _{LD}	° C		25	
Variant 2	T _{LD}	° C	15		35
Mode-hop free Power Range (SMSR $>$ 30 dB)					
Variant 0	Popt	mW		10	
Variant 1	Popt	mW	2		10
Variant 2	Popt	mW	2		10
Polarization Extinction Ratio	PER	dB		20	
Spatial Mode (transversal)				TEM ₀₀	

Measurement Conditions / Comments

Revision 0.94

see below
Temperature at Laser Chip
see order code scheme on p. 5
SMSR > 30 dB
see order code scheme on p. 5

 $P_{opt} = 10 \text{ mW}$ fundamental mode

 $U_R = 5 V$, target values

Monitor Diode

Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{opt}	µA / mW	1		20
Reverse Voltage Monitor Diode	U _{R MD}	V	3		5

Thermoelectric Cooler

Parameter	Symbol	Unit	min	typ	max
Current	I _{TEC}	А		0.4	
Voltage	U _{TEC}	V		0.8	
Power Dissipation (total loss at case)	Ploss	W		0.5	
Temperature Difference	ΔΤ	К			50

Thermistor (Standard NTC Type)

Parameter	Symbol	Unit	min	typ	max
Resistance	R	kOhm		10	
Beta Coefficient	β			3892	

Measurement Conditions / Comments

Conditions / Comments	
$\Delta T = 20 \text{ K}$	
∆T = 20 K	
∆T = 20 K	
$\Delta T = I T_{case} - T_{LD} I$	
	$\Delta T = 20 \text{ K}$ $\Delta T = 20 \text{ K}$ $\Delta T = 20 \text{ K}$

Measurement Conditions / Comments

© All rights reserved by eagleyard Photonics GmbH. This preliminary data sheet will be electronically administered and is subject to change without notice. Uncontrolled copy when printed. eagleyard Photonics GmbH

Rudower Chaussee 29 12489 Berlin GERMANY fon +49. 30. 6392 4520 fax +49. 30. 6392 4529

info@eagleyard.com www.eagleyard.com



EYP-DFB-0763-00010-1500-BFY02-0000



We focus on power.

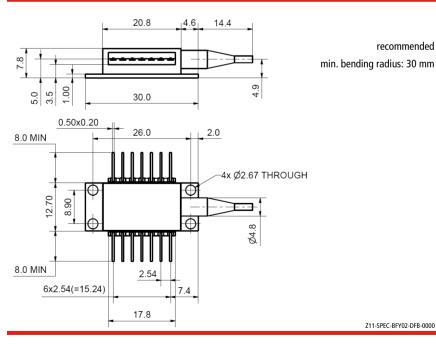
28.11.2011 Revision 0.94 page 3 from 5 DISTRIBUTED FEEDBACK LASER GaAs Semiconductor Laser Diode with integrated grating structure DFB/DBR Fiber and Connector Type Measurement Conditions / Comments PM Fiber 900 / 125 / 5.5 μ m, UV/Polyester-elastomer Coating (I = 1 +/-0.1 m) Connector different variants available see order code scheme ۲ FC/APC (narrow key / 2mm) • SC/APC ۲ other types on request

Package Pinout

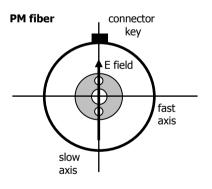
1	Thermoelectric Cooler (+)	14	Thermoelectric Cooler (-)
2	Thermistor	13	Case
3	Photodiode (Anode)	12	not connected
4	Photodiode (Cathode)	11	Laser Diode (Cathode)
5	Thermistor	10	Laser Diode (Anode)
6	not connected	9	not connected
7	not connected	8	not connected

Package Drawings

eagleyard Photonics GmbH



top view



slow axis of the PM fiber aligned to connector key

hermetically sealed Package: Leak Rate $< 5 \cdot 10^{-8}$ atm.cc./s acc. MIL-STD-883E

© All rights reserved by eagleyard Photonics GmbH. This preliminary data sheet will be electronically administered and is subject to change without notice. Uncontrolled copy when printed.

Rudower Chaussee 29 12489 Berlin GERMANY fon +49. 30. 6392 4520 fax +49. 30. 6392 4529

info@eagleyard.com www.eagleyard.com



EYP-DFB-0763-00010-1500-BFY02-0000



We focus on power.

DISTRIBUTED FEEDBACK LASER

GaAs Semiconductor Laser Diode

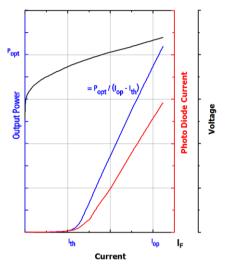
with integrated grating structure

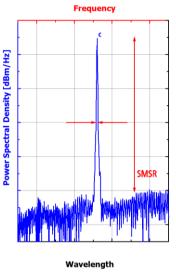


Typical Measurement Results

Output Power vs. Current

Spectra at Specified Optical Output Power





Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Ordering Information:



800 Village Walk #316 Guilford, CT 06437 Ph: 203-401-8093

Email orders to: sales@xsoptix.com Fax orders to: 800-878-7282



EYP-DFB-0763-00010-1500-BFY02-0000



We focus on power.

0 1

> 0 1 2

EYP-DFB-0763-00010-1500-BFY02- 0 x 0 x

	Revision 0.94	28.11.2011	page 5 from 5
DISTRIBUTED FEEDBACK LASER			
GaAs Semiconductor Laser Diode		<u></u>	
with integrated grating structure	RWE/RWL BAL	DFB/DBR	TPL/TPA

Order Code Scheme

Connector	
FC/APC (narrow key / 2mm)	
SC/APC	
other connector or fiber types upon request	

Mode-hop free Tuning Range (Minimum Side Mode Suppression Ratio > 30 dB)					
$P_{opt} = 10 \text{ mW};$	$T_{LD} = 25^{\circ}$	(Variant 0)			
$P_{opt} = 2 \dots 10 \text{ mW};$	$T_{LD} = 25^{\circ}$	(Variant 1)			
$P_{opt} = 2 \dots 10 \text{ mW};$	T _{LD} = 15° 35° C	(Variant 2)			

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The DFB diode type is known to be sensitive against optical feedback, so an optical isolator may be required in some cases. Operating at moderate temperatures on a proper metal heat sinks will contribute to stable operation and a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.



